

# Optimizing heat harvesting in a membrane based planar $\mu$ TEG: modelling and fabrication, & vice versa

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Optimizing heat harvesting in a membrane based planar µTEG: modelling and fabrication, & vice versa

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Micro-thermoelectric generators ( $\mu$ TEGs) are energy harvesting solutions to supply electrical power for autonomous microsystems and other miniature applications. We study here original all-Silicon  $\mu$ TEGs with a planar configuration in which the heat to harvest flows in-plane of a TE thin film. Such comparation in which the heat to narvest now in-plane of a 1 tc thin tills. Such planar modules are based on a polySi/Au thermopile periodically distributed onto dielectric membranes; a heat-collector permits to concentrate the energy to harvest onto half the junctions of the thermopile. This planar topology allows the implementation of thermocouples with a high aspect ratio compared to classical vertical TEGs. Heat concentrator is able to collect any form of lost heat (even evaporation enthalpy a priori, or radiation..)

#### 2. IEMN µTEG design & process

1<sup>st</sup> Initial design : semi-3D micro thermoelectric generator, planar structure. CMOS compatible process of microfabrication. Surface foot -print ~ 1/3 cm<sup>2</sup>, build up with 2 parts:

- Bottom part: N<sub>M</sub> membranes periodically etched in a Si(100) substrate & made of a dielectric bilayer (1,4µm SiO<sub>2</sub>/Si<sub>4</sub>N<sub>y</sub>). A poly-Silicon
- $\begin{array}{l} & (\mathbf{p}_i)_{i_1}, (\mathbf{p}_i)_{i_1}, (\mathbf{p}_i)_{i_2}, (\mathbf{p$ \* The pSi width (L =50, 70 or 200 µm) is larger than the Au plated parts (10 µm)  $\rightarrow$  this **modulated-width** thermopile has a reduced
- internal electrical resistance R<sub>INT</sub> → electrical & thermal simulations show a gain in output power generated for larger stripes \* The TC number, N, is a function of  $N_M$  and L: N= x.N<sub>M</sub> (x =144, 112, 46 for L=50, 70, 200 $\mu$ ). For fixed L, R<sub>INT</sub> is the same.
- \* The whole is covered with a 15µm thick PolyImide layer (robustness & electrical isolation): 15µm is a compromise (for 2m-µG up thigher  $\Delta T$  for 30µm PI but the benefice fastly diminish with N<sub>M</sub> for 10µTEG it is even worse; see evolution in figure section 4.c/...)
- Second part : heat concentrator HC (surf=0.3cm<sup>3</sup>) also fabricated starting from Si(100). It has as much pillars ( $N_{sd}$ ) as there are membranes (200µm thick, 5.1 mm long & width optimised versus  $N_{ub}$ ). Pillars canalyze the heat flow to harvest ( $\Phi$ , that arrives on its surface) into half of the thermopile junctions. A periodical  $\Delta T$  is created at each TC. The HC has also 4 bosses at its corners (mechanical stability, avoid membranes breaking) that short-cut one part of  $\Phi$ 
  - $\Phi_{\text{Total}} \Phi_{\text{Piller}} + \Phi_{\text{Borner}} + \Phi_{\text{convection}} + \Phi_{\text{convition}}$





mental thermopile internal electrical res contains a non negligible contribution fro istance (between thermoelements) stance µTEGs with codoped pSi : not taken into account → For a fixed amount of heat to harvest, 5-membranes µTEGs are confin

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→ However, in any case, these values are low because of large internal electrical resistance R<sub>INT</sub> of the thermopiles pSi/Au.

#### 4. Thermal Modelling - Reducing heat losses & considering superior TE layer properties

Renewed design to improve the performance: a few routes to be validated by forthcoming experiments

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• 4.A/ 3D thermal modelling using COMSOL Multiphysics®, 4.D/ Modelling the impact of TE thermal conductivity & optimisation of generated output power ermal heat flux 👁 b/ Considering different TE layers with different thermal conductivities  $\lambda$ 4 a/ Considering a metal TE layer with good PF and which impless R.... (reduced value and no parasitic contact resistance) Preliminary test validate higher A tantan/Metal TC are being tested (2019 – 2020) A STATE → C tan/Au thermopile λ= 4  $\Delta T_{cf}$  to be generated as a function of input heat to harvest trimental codoping →To be confirmed nanost ed TE λ= 20 Most of our classical cas Geometry of half µTEG (here 5 membranes) Mesh Evaluation of Temperature  $\Delta T$  generated for  $\Phi$ = 1W input heat λ= 31.4 (¥) λ= 60 100 A heat flux of 1W is applied on the concentrator surface and the Poly-Silicon AT er (M) AT.ac 90 poly-Si ?! VS TE laver A temperature of the backside of the Si substrate is kept at 293 K (RT). λ= 140 Si single crystal An equivalent layer is considered to Account for multi-layer membranes 70 2 25 3 35  $\lambda_{cq}e_{cq} = \lambda_{Slo_2}e_{Slo_2} + \lambda_{Sl_xN_y}e_{Sl_xN_y} + \lambda_{polysi}e_{polysi} + \frac{l_{polysi} + l_{Au}}{l_{polysi} + l_{Au} + 2i} + \lambda_{Au}e_{Au}\frac{l_{Au}}{l_{polysi} + l_{Au} + 2i}$ 60  $\rightarrow$  V<sub>S</sub>= N.  $\alpha_{Cn/Au} \Delta T$  4.B/ Geometrical structure optimisation (Φ=1W) 40  $\Delta T_{cf}$  versus pillar width, w, for  $\mu$ TEG with 2 to 10 membranes  $N_m \times \Delta T_{cf}$  versus w  $\rightarrow$  indicative of  $P_{MAX}$ = V<sub>S<sup>2</sup></sub> / 4. R<sub>ib</sub> 20 TE thermal conductivity  $\lambda$  (W/K/m) .... 8,, Case Constatan/Au: 600/2 <u>Lase Constantinue</u> Bool/250ml
<u>Cases for TE Layers with PF & or 21</u>:
—Experimental points: *p* and *n* type polySi as for *p*-pSi loyer en<sub>e</sub>-280mm, an extrapolation for 600nm is calculate ---Nanostructured TE layer taken with \u03c6 = 4 W/K/m -100 200 300 400 500 600 700 Largeur des piliers (µm) With a nanostructured TE layer ( $\lambda = 4 \& PF = 21$ ) the max output power would be > 0,5mW/cm<sup>2</sup> for  $\Phi=1W$  heat input Any new polySi would be interesting if it combines low  $\lambda$  (<10W/K/m) and large PF (>15 $\mu$ W/K<sup>3</sup>/cm) in order the  $\mu$ TEGs to perform equivalently or better than the theoretical Cn/Au case ... The difference of temperature at each TC in the thermopile has a maximum at an optimum pillar width value • The difference of temperature being higher for µTEGs with 4 membranes , these latter will have the • 4.C/ Reducing the heat lost in highest thermal resistance  $r_{TH}$  compared to  $5m-\mu TEG$   $\rightarrow$  to be taken into account in future design **5** - Conclusions the bosses of the heat-concentrator All-Silicon planar μTEG with a modular thermal resistance (11-113 K/W) are fabricated by CMOS compatible microtechnology, integrating a thermopile built up with micro/nano-structured polySi as TE material. The number of membranes on which is periodically laying the thermopile can be varied and the heat to harvest is collected through a pillar-based Si-concentrator. The weak point of our μTEGs is their high internal electrical resistance: P<sub>MAX</sub> are moderate: up to 62µW/cm<sup>2</sup>, 164µW/cm<sup>2</sup>, and 86 µW/cm<sup>2</sup>, for respectively 2, 5 or 10 membranes μTEGs (1W heat injected). Reducing  $\Phi_{\text{Basses}}$  by lowering bosses thermal conductivity: done via local fabrication of Porous Silicone by anodization then oxidization (annealing at high temperature) The difference of temperature  $\Delta T$  can be up to 28% higher (in 2m-µTEGs) with 150µm thick porous-Si bosses  $\rightarrow$  it should be possible to increase P<sub>MAX</sub> by up to 64% λ<sub>si</sub> = 140 W/m/K VERSUS λ<sub>porous-Si oxidized</sub> ~ 1 W/m/K To better clarify further improvements to be carried out, while keeping the high r<sub>ru</sub> values, COMSOL 3D thermal simulation was done for different new Porous boss Pillars of the - the optimum membrane number is 4 (not 5): same  $P_{MAX}$  and higher  $r_{TH}$ - use larger stripe (L=200µm versus currently 70µm) should be considered (20% increase in  $P_{MAX}$ ) Better dimensioning: - the optim 1/0 160 **ΔT**  Higher Power Factor (PF) effect: considering a thermopile integrating a Constantan layer can double P<sub>MAX</sub> (~300 µW/cm<sup>2</sup> for 1W injected). Compared to modules with *non optimum polysi* (i.e. with PF < 10 µW/k<sup>2</sup>m or so) this represent a reliable way to enhance P<sub>MAX</sub> by a factor of up to 3. However this is only valid for a Tstripe width of L=50 µm (for larger 1t discresse).
>> this is being evaluated (together with 4-membranes configuration and porous bosses in the heat-concentrator) Temperature distribution in a half 2m-μTEG when op) bosses are normal & (bottom) when bosses are made of porous-Si 10m-uG High PF but bad microstructure of the TE layer : it results in poorer module performance ("cold case" explained : codoped polySi layer may have λ> 60W/K/m...) Considering nanostructured TE layer with a thermal conductivity  $\lambda$  reduced by a factor of 10 compared to polySi (ie even better than Cn) should result in a higher  $\Delta$ T (24,6% for Sm\_TEG), so in a  $T_{Max}$ ,6% higher (assuming same PF as our best p-type polySi)  $\rightarrow$  in such cases 550-660 µµ(cm)<sup>RD</sup> should be obtained for a Sm\_TEG harvesting 140 µµmut heat. ating the influence of two thicknesses : I/ of porous bosses and II/ of polyimide protection layer che et al. JMEMS 26,087003 (2017) 45 grisona et al., 14th Eur. Thermoelectric Conf. (2016), Lisboa n et al. , Sensors and Actuators, A 221 (2015) 67 al c ISEN Université Ø .

# 3. Characterisation of µTEG performance